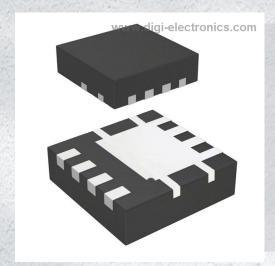


# DMP3008SFGQ-7 Datasheet



https://www.DiGi-Electronics.com

DiGi Electronics Part Number DMP3008SFGQ-7-DG

Manufacturer Diodes Incorporated

Manufacturer Product Number DMP3008SFGQ-7

Description MOSFET P-CH 30V 8.6A PWRDI3333-8

Detailed Description P-Channel 30 V 8.6A (Ta) 900mW (Ta) Surface Mou

nt POWERDI3333-8



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RFQ Email: Info@DiGi-Electronics.com

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# **Purchase and inquiry**

Manufacturer Product Number:	Manufacturer:
DMP3008SFGQ-7	Diodes Incorporated
Series:	Product Status:
	Active
FET Type:	Technology:
P-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
30 V	8.6A (Ta)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
4.5V, 10V	17m0hm @ 10A, 10V
Vgs(th) (Max) @ ld:	Gate Charge (Qg) (Max) @ Vgs:
2.1V @ 250µA	47 nC @ 10 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±20V	2230 pF @ 15 V
FET Feature:	Power Dissipation (Max):
	900mW (Ta)
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Surface Mount
Supplier Device Package:	Package / Case:
PowerDI3333-8	8-PowerVDFN
Base Product Number:	
DMD2000	

# **Environmental & Export classification**

8541.21.0095

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	





# 30V P-CHANNEL ENHANCEMENT MODE MOSFET PowerDI®

#### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = 25°C
	17mΩ @ V <sub>GS</sub> = -10V	-8.6A
-30V	25mΩ @ V <sub>GS</sub> = -4.5V	-7.1A

### **Features and Benefits**

- Low R<sub>DS(ON)</sub> Ensures On-State Losses are Minimized
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies Just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

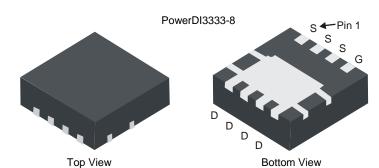
## **Description and Applications**

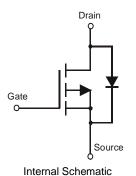
This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- Power Management Functions
- DC-DC Converters

#### **Mechanical Data**

- Case: PowerDI<sup>®</sup>3333-8
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
   Solderable per MIL-STD-202. Method 208 @3
- Weight: 0.008 grams (Approximate)





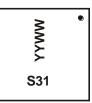
### Ordering Information (Note 5)

Part Number	Case	Packaging
DMP3008SFGQ-7	PowerDI3333-8	2,000/Tape & Reel
DMP3008SFGQ-13	PowerDI3333-8	3,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product\_compliance\_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



S31 = Product Type Marking Code YYWW = Date Code Marking YY = Last digit of year (ex: 11 = 2011) WW = Week code (01 ~ 53)



# Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage		V <sub>DSS</sub>	-30	V	
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Steady $T_A = +25^{\circ}C$ State $T_A = +70^{\circ}C$		* *	I <sub>D</sub>	-8.6 -7.0	А
Continuous Drain Current (Note 7) V <sub>GS</sub> = -10V	t<10s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I <sub>D</sub>	-11.7 -9.3	А
Continuous Drain Current (Note 7) $V_{GS}$ = -4.5V State $T_A$ = +25°C $T_A$ = +70°C $T_A$ = +25°C $T_A$ = +25°C $T_A$ = +70°C		I <sub>D</sub>	-7.1 -5.6	А	
		, ,	I <sub>D</sub>	-9.6 -7.6	А
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I <sub>DM</sub>	-80	Α
Maximum Continuous Body Diode Forward Current (Note 7)			I <sub>S</sub>	-3.0	Α

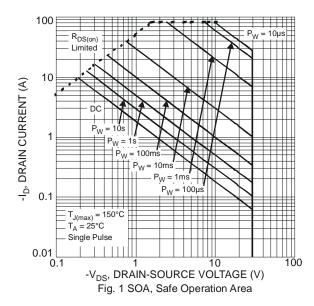
## **Thermal Characteristics**

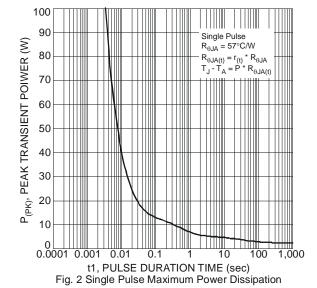
Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 6)		$P_D$	0.9	W
Thormal Basistanas, Junatian to Ambient (Note 6)	Steady State	7	140	°C/W
Thermal Resistance, Junction to Ambient (Note 6)		$R_{\theta JA}$	72	°C/W
Total Power Dissipation (Note 7)		$P_D$	2.2	W
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	D	57	°C/W
t<10s		$R_{\theta JA}$	30	°C/W
Thermal Resistance, Junction to Case (Note 7)		$R_{ heta JC}$	7.1	°C/W
Operating and Storage Temperature Range		$T_{J_i}T_{STG}$	-55 to +150	°C

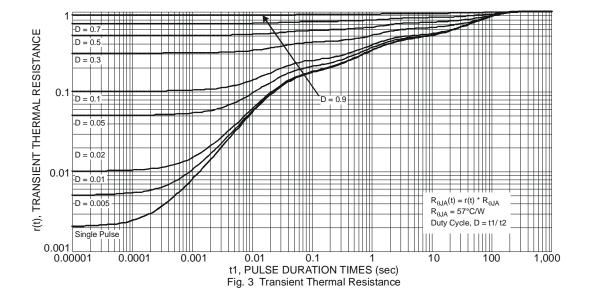
es: 6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

<sup>7.</sup> Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.











# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

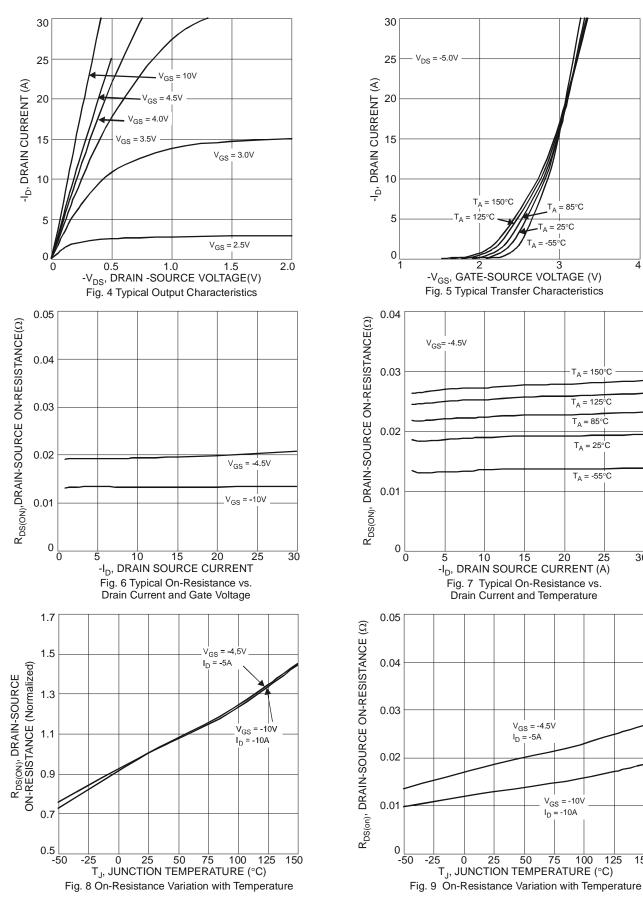
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-30	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	-1.0	μΑ	$V_{DS} = -30V, V_{GS} = 0V$
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	-1.1	-1.6	-2.1	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$
Static Drain-Source On-Resistance			12.5	17	mΩ	$V_{GS} = -10V, I_D = -10A$
Static Diain-Source On-Nesistance	R <sub>DS(ON)</sub>		18.5	25	11122	$V_{GS} = -4.5V, I_D = -10A$
Forward Transfer Admittance	Y <sub>fs</sub>	_	13	_	S	$V_{DS} = -15V, I_{D} = -10A$
Diode Forward Voltage	$V_{SD}$	_	-0.7	-1.0	V	$V_{GS} = 0V, I_{S} = -1A$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	Ciss	_	2,230	_		V 45V V 6V
Output Capacitance	Coss		328	_	pF	$V_{DS} = -15V, V_{GS} = 0V$ f = 1.0MHz
Reverse Transfer Capacitance	$C_{rss}$		294	_		1 = 1.01/1112
Gate Resistance	Rg	_	6.4	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$
Total Gate Charge (V <sub>GS</sub> = -10V)	Qg	_	47	_		
Total Gate Charge (V <sub>GS</sub> = -4.5V)	Qg	_	23	_	nC	\\\ 45\\ I 400
Gate-Source Charge	Qgs	_	9.4	_	iiC	$V_{DS} = -15V, I_{D} = -10A$
Gate-Drain Charge	Q <sub>gd</sub>	_	5.6	_		
Turn-On Delay Time	t <sub>D(ON)</sub>	_	10.5	_		
Turn-On Rise Time	t <sub>R</sub>		8.5		nS	V 10V V 15V D 00
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	90	_	113	$V_{GS} = -10V, V_{DS} = -15V, R_G = 6\Omega$
Turn-Off Fall Time	t <sub>F</sub>	_	40	_	1	

Notes:

<sup>8.</sup> Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.







# **DKODES**

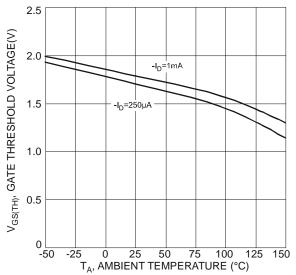
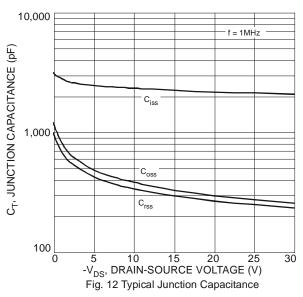
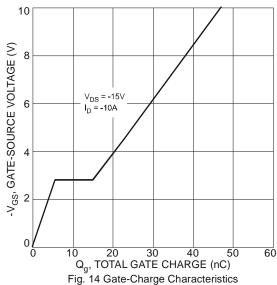


Fig. 10 Gate Threshold Variation vs. Ambient Temperature





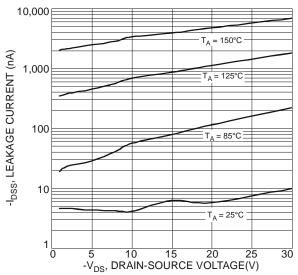


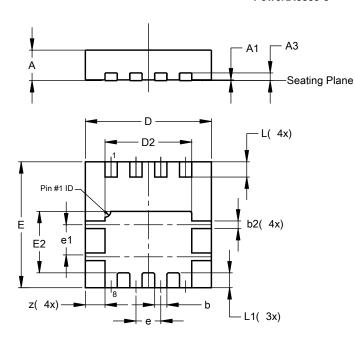
Fig. 13 Typical Drain-Source Leakage Current vs. Voltage



## **Package Outline Dimensions**

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

#### PowerDI3333-8

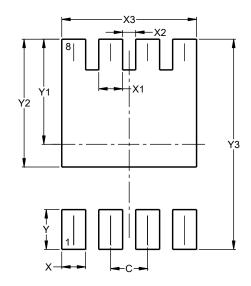


PowerDI3333-8					
Dim	Min	Max	Тур		
Α	0.75	0.85	0.80		
A1	0.00	0.05	0.02		
A3	_	_	0.203		
b	0.27	0.37	0.32		
b2	_	_	0.20		
D	3.25	3.35	3.30		
D2	2.22	2.32	2.27		
E	3.25	3.35	3.30		
E2	1.56	1.66	1.61		
е	_	_	0.65		
e1	0.79	0.89	0.84		
L	0.35	0.45	0.40		
L1	_	_	0.39		
Z	_	_	0.515		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

#### PowerDI3333-8



Dimensions	Value (in mm)
С	0.650
X	0.420
X1	0.420
X2	0.230
Х3	2.370
Υ	0.700
Y1	1.850
Y2	2.250
Y3	3.700



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